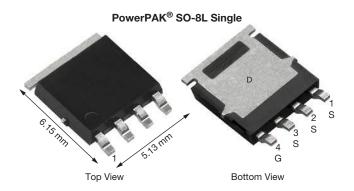


www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	40		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0070		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0095		
I _D (A) per leg	30		
Configuration	Single		
Package	PowerPAK SO-8L		

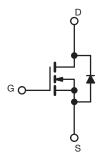
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



N-Channel MOSFET

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	40		
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current ^a	T _C = 25 °C	1	30		
	T _C = 125 °C	I _D	30		
Continuous source current (diode conduction) ^a		I _S	30	Α	
Pulsed drain current ^b		I _{DM}	110		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	26	I	
Single pulse avalanche energy	L = U. I IIII	E _{AS}	33.8	mJ	
Maximum power dissipation ^b	T _C = 25 °C	P _D	48	W	
	T _C = 125 °C		16		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260	·	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount c	R _{thJA}	70	°C/W		
unction-to-case (drain)		R_{thJC}	3.1	C/ VV		

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							•
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		1.5	2.0	2.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
Drain-source on-state resistance ^a	. ,	V _{GS} = 10 V	I _D = 8 A	-	0.0058	0.0070	Ω
	D	V _{GS} = 4.5 V	I _D = 6 A	-	0.0079	0.0097	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 8 A, T _J = 125 °C	-	-	0.0101	
		V _{GS} = 10 V	I _D = 8 A, T _J = 175 °C	-	-	0.0120	
Forward transconductance b	9fs	V _{DS} = 15 V, I _D = 8 A		-	49	-	S
Dynamic ^b							
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	1350	1800	pF
Output capacitance	Coss	$V_{GS} = 0 V$		-	850	1150	
Reverse transfer capacitance	C _{rss}			-	40	55	
Total gate charge ^c	Q_g			-	21	35	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$ $V_{DS} = 20 \text{ V}, I_D = 4 \text{ A}$		-	5	-	nC
Gate-drain charge ^c	Q _{gd}			-	3	-	
Gate resistance	R_g	f = 1 MHz		0.6	1.3	2.0	Ω
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = 20 \text{ V, } R_L = 5 \Omega$ $I_D \cong 4 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	12	20	ns
Rise time ^c	t _r			-	4	10	
Turn-off delay time ^c	t _{d(off)}			-	25	40	
Fall time ^c	t _f			-	6	10	
Source-Drain Diode Ratings and Chara	cteristics b						
Pulsed current ^a	I _{SM}			-	-	110	Α
Forward voltage	V_{SD}	I _F = 8 A, V _{GS} = 0 V		-	0.81	1.2	V
Body diode reverse recovery time	t _{rr}	I _F = 5 A, di/dt = 100 A/μs		-	44	90	ns
Body diode reverse recovery charge	Q_{rr}			-	42	90	nC
Reverse recovery fall time	ta			-	22	-	ns
Reverse recovery rise time	t _b			-	22	-	
Body diode peak reverse recovery	I _{RM(REC)}			_	-1.8	_	А

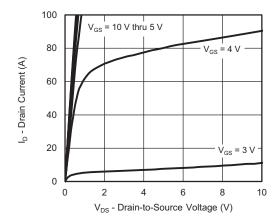
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

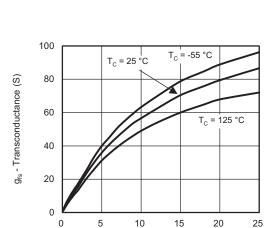
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

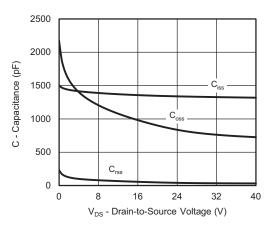


Output Characteristics

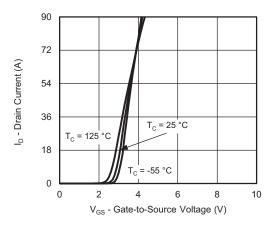


Transconductance

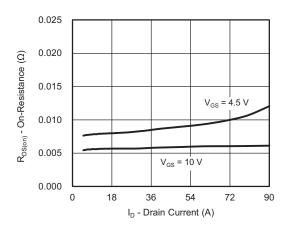
I_D - Drain Current (A)



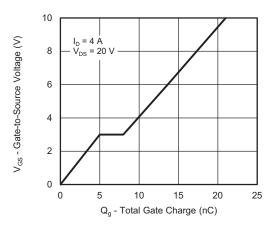
Capacitance



Transfer Characteristics



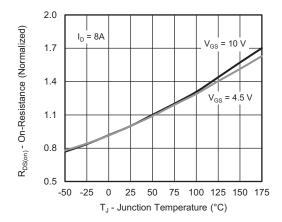
On-Resistance vs. Drain Current



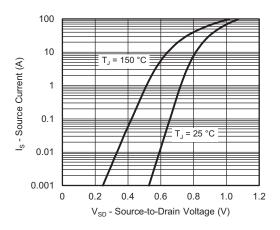
Gate Charge



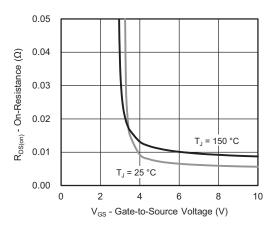
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



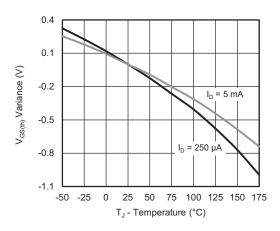
On-Resistance vs. Junction Temperature



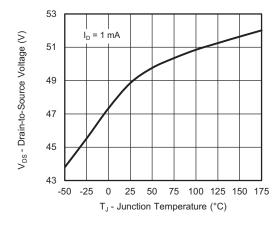
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



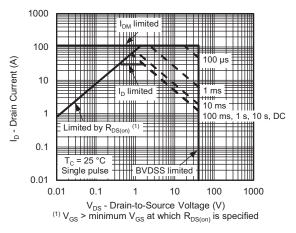
Threshold Voltage



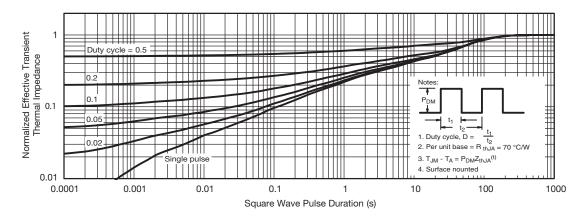
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



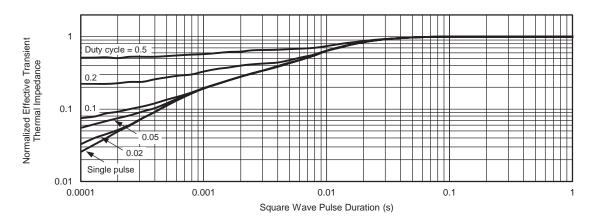
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75564.



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Vishay manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201

JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DLE 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1

RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3 2SK2614(TE16L1,Q)